

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	PBSS5350T
▶ Overseas	Part Number	PBSS5350T
▶ Equivalent	Part Number	PBSS5350T

EV is the abbreviation of name EVVO

Descriptions

Silicon PNP transistor in a SOT-23 Plastic Package.

Features

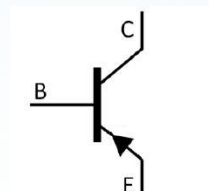
Low $V_{CE(sat)}$, high current.

Applications

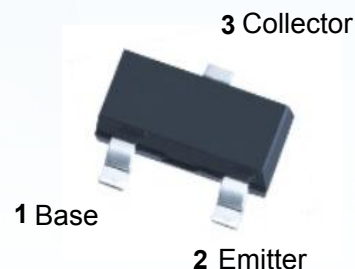
General purpose switching and muting

LCD back-lighting

Supply line switching circuits.



SOT23



h_{FE} Classifications & Marking

h_{FE} Range	>200
Marking	ZDW

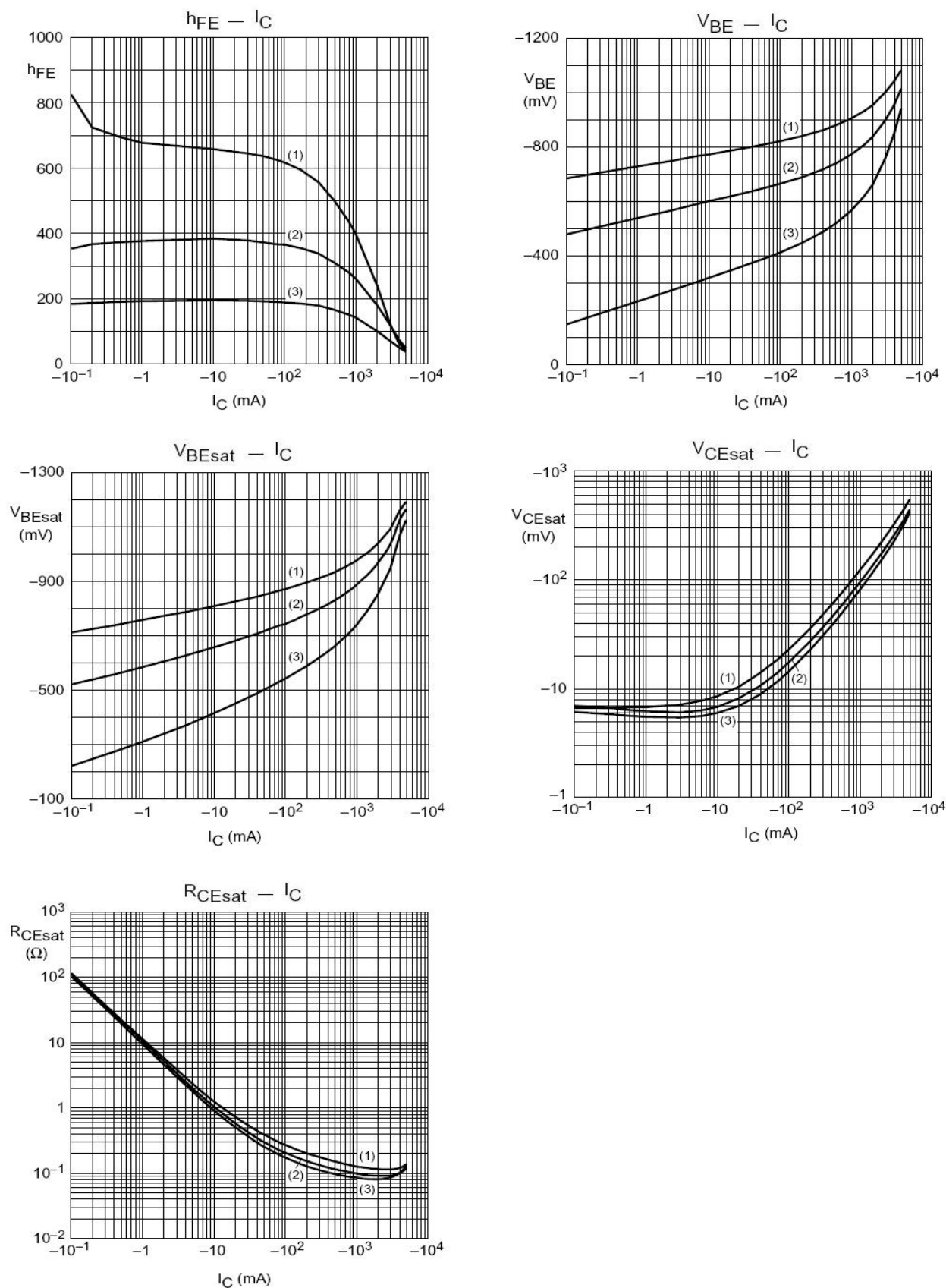
Absolute Maximum Ratings($T_a=25^{\circ}\text{C}$)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-2	A
Peak Collector Current	I_{CM}	-5	A
Base Current	I_B	-0.5	A
Total Power Dissipation	P_{tot}	300	mW
Total Power Dissipation	P_{tot} (註 1、2)	1.2	W
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-65~150	$^{\circ}\text{C}$

Electrical Characteristics(Ta=25°C)

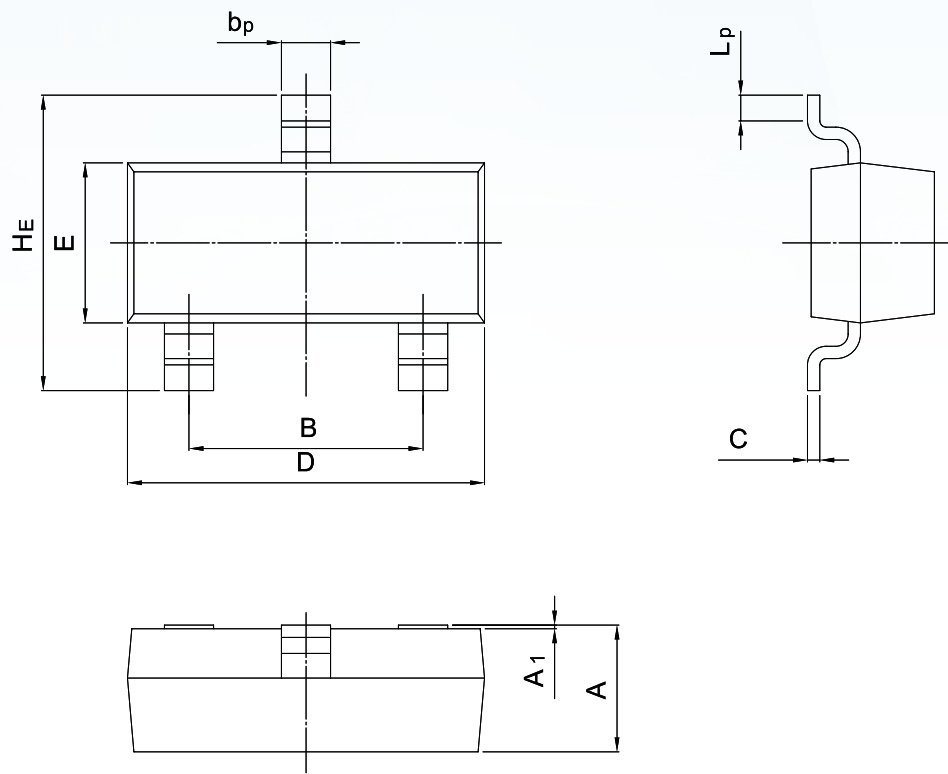
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-50V$ $I_E=0$			-100	nA
		$V_{CB}=-50V$ $I_E=0$ $T_j=150^{\circ}C$			-50	μA
emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-100	nA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-2.0V$ $I_C=-100mA$	200			
	$h_{FE(2)}$	$V_{CE}=-2.0V$ $I_C=-500mA$	200			
	$h_{FE(3)*}$	$V_{CE}=-2.0V$ $I_C=-1.0A$	200			
	$h_{FE(4)*}$	$V_{CE}=-2.0V$ $I_C=-2.0A$	130			
	$h_{FE(5)*}$	$V_{CE}=-2.0V$ $I_C=-3.0A$	80			
Collector-Emitter Saturation Voltage	$V_{CE(sat)(1)*}$	$I_C=-500mA$ $I_B=-50mA$			-80	mV
	$V_{CE(sat)(2)*}$	$I_C=-2.0A$ $I_B=-100mA$			-320	mV
Equivalent On-Resistance	$R_{CE(sat)*}$	$I_C=-2.0A$ $I_B=-200mA$		90	135	m Ω
Base-Emitter Saturation Voltage	$V_{BE(sat)*}$	$I_C=-2.0A$ $I_B=-100mA$			-1.1	V
		$I_C=-3.0A$ $I_B=-300mA$			-1.2	V
Base-Emitter Voltage	$V_{BE(ON)*}$	$V_{CE}=-2.0V$ $I_C=-1.0A$			-1.2	V
Transition Frequency	f_T	$V_{CE}=-5.0V$ $f=100MHz$ $I_C=-100mA$	100			MHz
Collector Capacitance	C_C	$V_{CB}=-10V$ $I_E=0$ $f=1.0MHz$			35	pF

Electrical Characteristic Curve

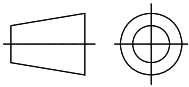


PACKAGE OUTLINE
Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	bp	C	D	E	H	A1	Lp
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20



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